

GNP POLI - 610



I n t e l l i g e n t C M P S y s t e m F o r R e s e a r c h & D e v e l o p m e n t G & P T e c h n o l o g y

SPECIFICATIONS

- Head, Table 30 ~ 200 rpm, Rotational motion, Head oscillation (± 12 mm)
- Size 1,200W 1,290D 1,960Hmm
- Platen size $\varnothing 623$ mm (25 inch), Anodized Aluminum (Option : Teflon Coated)
- Pressing method Variable air pressure electronic controller
 - Carrier Type : 350kgf
 - Wafer Down Force & Conditioning Load Monitoring System
- Process Automatic sequence, Dry-in / Wet-out

OPTIONS

- Pad Conditioning Method : Oscillation Head Type
- Double Head System
- Friction Force & Temperature Monitoring System

APPLICATIONS

- Workpiece Max 8 ea of 3inch wafers/run, Max 6 ea of 4inch wafers/run
- CMP Process CMP for compound wafers including SiC, GaN and sapphire, etc.

CHARACTERISTICS

- Stable repeatability (WTWNU < 5%)
- High rigidity